Amendments to the Specification:

Please replace the Abstract on page 20 with the following rewritten Abstract:

A method of forming shallow trench isolation ~~using CMP is described. A pad oxide layer is grown overlying a silicon semiconductor substrate. A polysilicon layer is deposited overlying the pad oxide layer. A nitride layer is deposited overlying the polysilicon layer. Trenches are etched~~ includes etching trenches through ~~the~~ a nitride layer, a polysilicon layer, and a pad oxide layer and into ~~the silicon~~ a semiconductor substrate. ~~and filled~~ The trenches are filled with an oxide layer. ~~In one alternative, a~~ A silicon oxynitride layer is deposited overlying the oxide layer. ~~A first polishing is performed to polish away the silicon oxynitride layer and oxide layer~~ and both these layers are polished away using a first slurry having high selectivity ~~of oxide to nitride~~. A second polishing ~~is performed to polish~~ polishes away the oxide layer using a second slurry having a low selectivity ~~of oxide to nitride and having low defect properties~~. The nitride layer is removed and a third polishing is performed to planarize the oxide layer using a third slurry having high selectivity ~~of oxide to polysilicon to complete formation of shallow trench isolations~~. ~~In a second alternative~~ Alternatively, the oxide layer is etched away except where it overlies the trenches. A first polishing is performed to polish away the oxide layer using a first slurry having a low selectivity ~~of oxide to nitride and having low defect properties~~. A second polishing is performed to polish away the oxide layer using a second slurry having high selectivity ~~of oxide to nitride to complete STI formation~~.

After the title, please replace the benefit claim with the following redrafted benefit claim:

This is a divisional of Patent Application serial number 09/981,436, filing date 10/18/01, now U.S. Patent 6,638,866, entitled A Novel Chemical-Mechanical Polishing (CMP) Process For Shallow Trench Isolation, assigned to the same assignee as the present application.